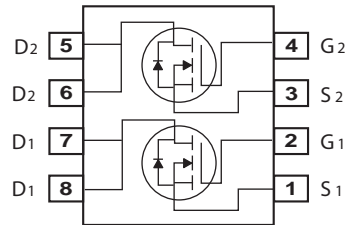
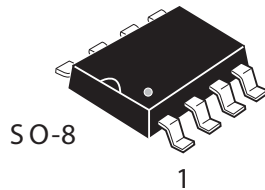


**Dual N-Channel Enhancement Mode Field Effect Transistor****PRODUCT SUMMARY**

V <sub>DSS</sub>	I <sub>D</sub>	R <sub>DS(ON)</sub> (mΩ) Max
30V	6.5A	32 @ V <sub>GS</sub> =10V
		52 @ V <sub>GS</sub> =4.5V

**FEATURES**

- Super high dense cell design for low R<sub>DS(ON)</sub>.
- Rugged and reliable.
- Surface Mount Package.

**ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Limit	Units
V <sub>DS</sub>	Drain-Source Voltage	30	V
V <sub>GS</sub>	Gate-Source Voltage	±20	V
I <sub>D</sub>	Drain Current-Continuous <sup>a</sup>	T <sub>A</sub> =25°C	6.5
		T <sub>A</sub> =70°C	5.2
I <sub>DM</sub>	-Pulsed <sup>b</sup>	24	A
P <sub>D</sub>	Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> =25°C	2
		T <sub>A</sub> =70°C	1.28
T <sub>J</sub> , T <sub>STG</sub>	Operating Junction and Storage Temperature Range	-55 to 150	°C

**THERMAL CHARACTERISTICS**

R <sub>θJA</sub>	Thermal Resistance, Junction-to-Ambient <sup>a</sup>	62.5	°C/W
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## ELECTRICAL CHARACTERISTICS (T<sub>A</sub>=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V , I <sub>D</sub> =250uA	30			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =24V , V <sub>GS</sub> =0V			1	uA
I <sub>GSS</sub>	Gate-Body Leakage Current	V <sub>GS</sub> = ±20V , V <sub>DS</sub> =0V			±100	nA
ON CHARACTERISTICS						
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	1	1.9	3	V
R <sub>DS(ON)</sub>	Drain-Source On-State Resistance	V <sub>GS</sub> =10V , I <sub>D</sub> =6.5A		26	32	m ohm
		V <sub>GS</sub> =4.5V , I <sub>D</sub> =5.1A		40	52	m ohm
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> =5V , I <sub>D</sub> =6.5A		7		S
DYNAMIC CHARACTERISTICS <sup>°</sup>						
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =15V,V <sub>GS</sub> =0V f=1.0MHz		513		pF
C <sub>oss</sub>	Output Capacitance			91		pF
C <sub>rSS</sub>	Reverse Transfer Capacitance			73		pF
SWITCHING CHARACTERISTICS <sup>°</sup>						
t <sub>D(ON)</sub>	Turn-On Delay Time	V <sub>DD</sub> =15V I <sub>D</sub> =1A V <sub>GS</sub> =10V R <sub>GEN</sub> =6 ohm		10		ns
t <sub>r</sub>	Rise Time			11		ns
t <sub>D(OFF)</sub>	Turn-Off Delay Time			17.5		ns
t <sub>f</sub>	Fall Time			10.5		ns
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> =15V,I <sub>D</sub> =6.5A,V <sub>GS</sub> =10V		9.2		nC
		V <sub>DS</sub> =15V,I <sub>D</sub> =6.5A,V <sub>GS</sub> =4.5V		4.7		nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>DS</sub> =15V,I <sub>D</sub> =6.5A,		1.3		nC
Q <sub>gd</sub>	Gate-Drain Charge	V <sub>GS</sub> =4.5V		2.7		nC
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
I <sub>s</sub>	Maximum Continuous Drain-Source Diode Forward Current				2	A
V <sub>SD</sub>	Diode Forward Voltage <sup>b</sup>	V <sub>GS</sub> =0V,I <sub>s</sub> =2A		0.82	1.2	V

### Notes

- a.Surface Mounted on FR4 Board,t < 10sec.  
b.Pulse Test:Pulse Width < 300us, Duty Cycle < 2%.  
c.Guaranteed by design, not subject to production testing.

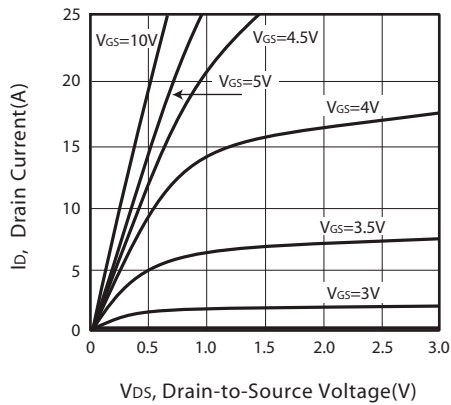


Figure 1. Output Characteristics

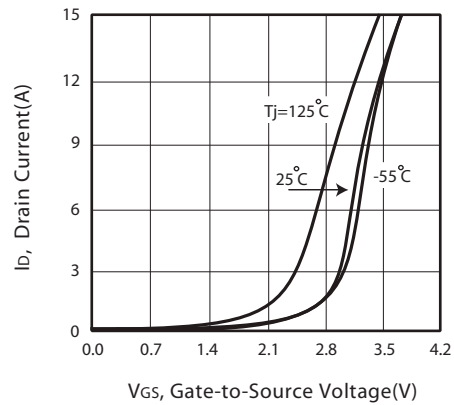


Figure 2. Transfer Characteristics

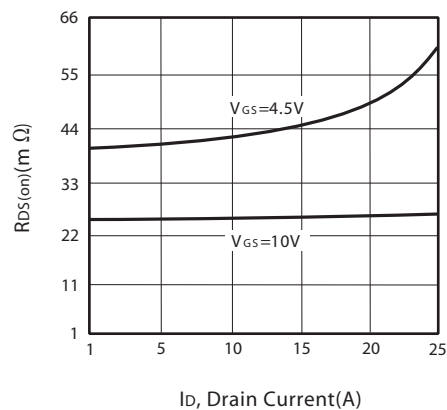


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

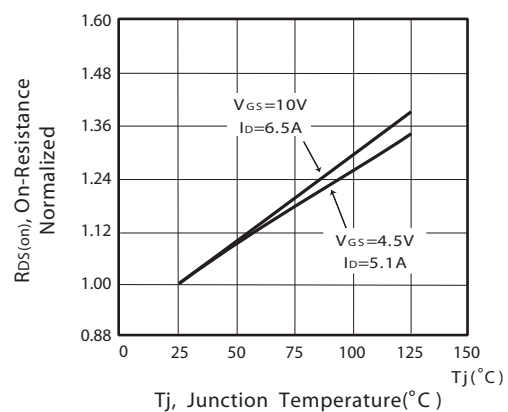


Figure 4. On-Resistance Variation with Drain Current and Temperature

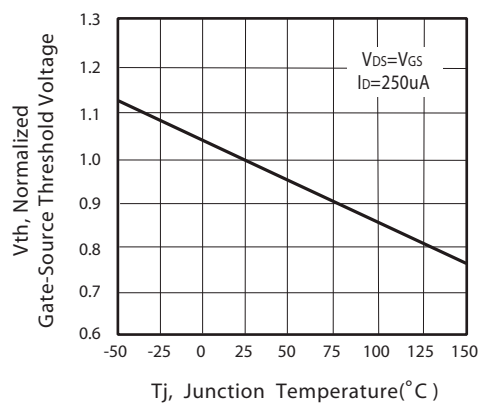


Figure 5. Gate Threshold Variation with Temperature

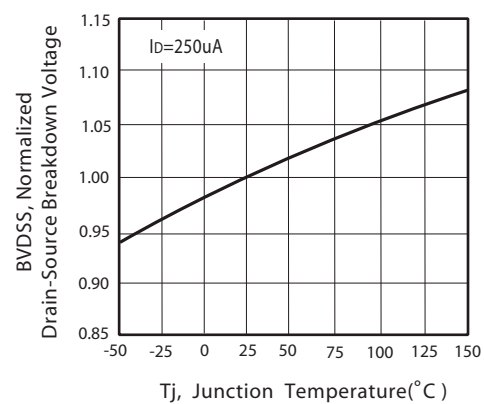


Figure 6. Breakdown Voltage Variation with Temperature

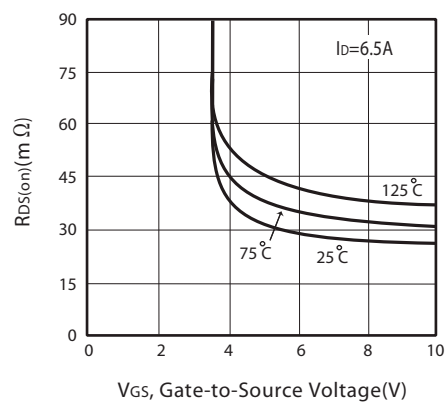


Figure 7. On-Resistance vs. Gate-Source Voltage

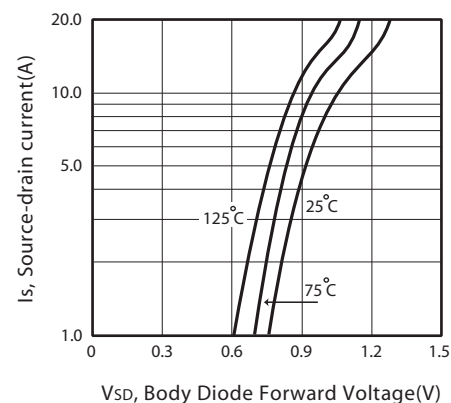


Figure 8. Body Diode Forward Voltage Variation with Source Current

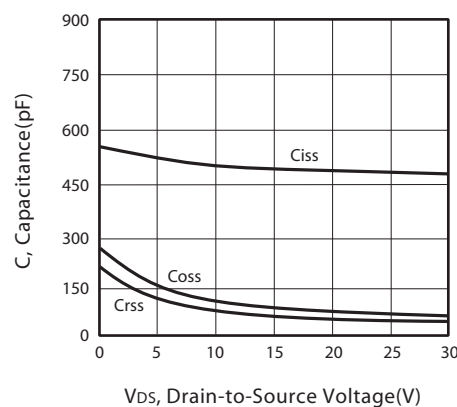


Figure 9. Capacitance

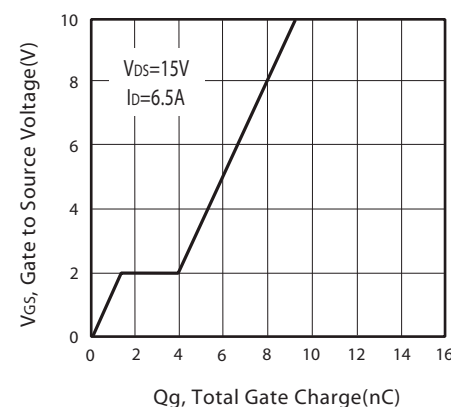


Figure 10. Gate Charge

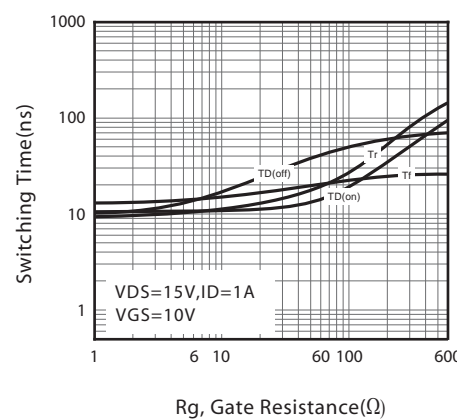


Figure 11. switching characteristics

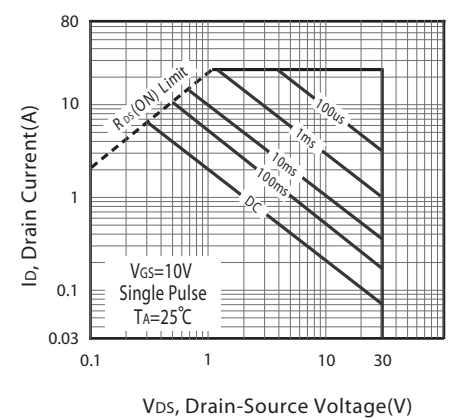
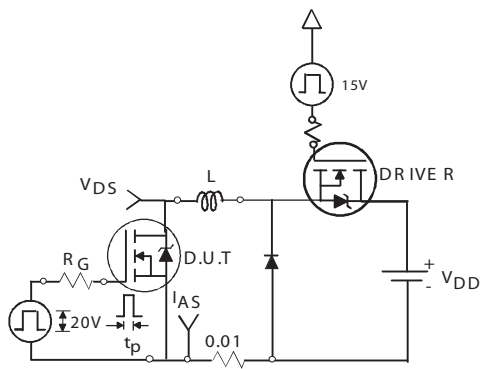
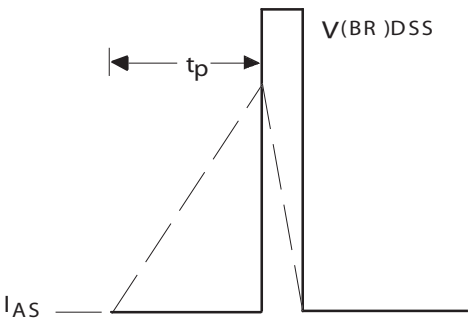


Figure 12. Maximum Safe Operating Area



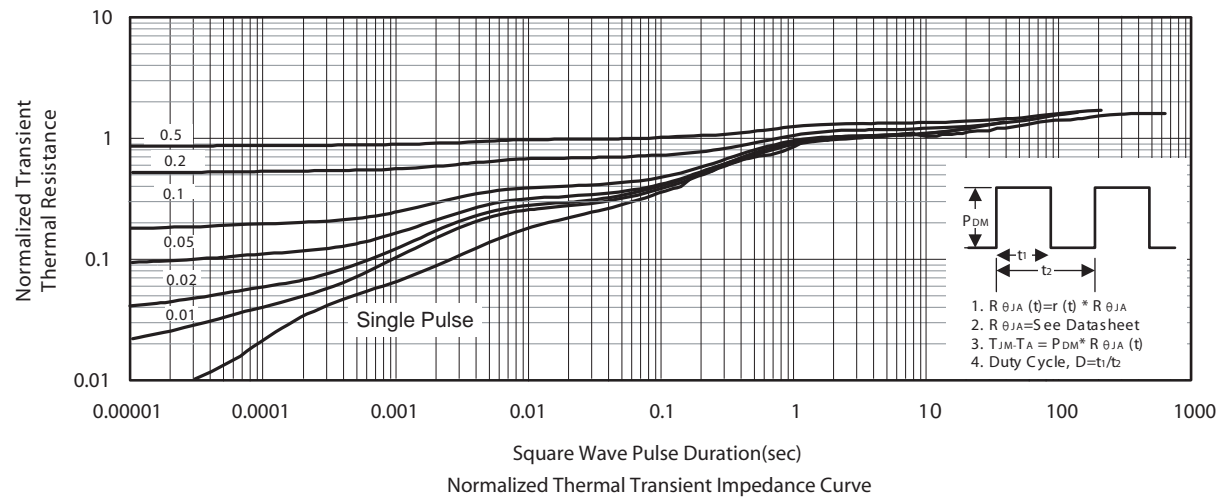
Unclamped Inductive Test Circuit

Figure 13a.



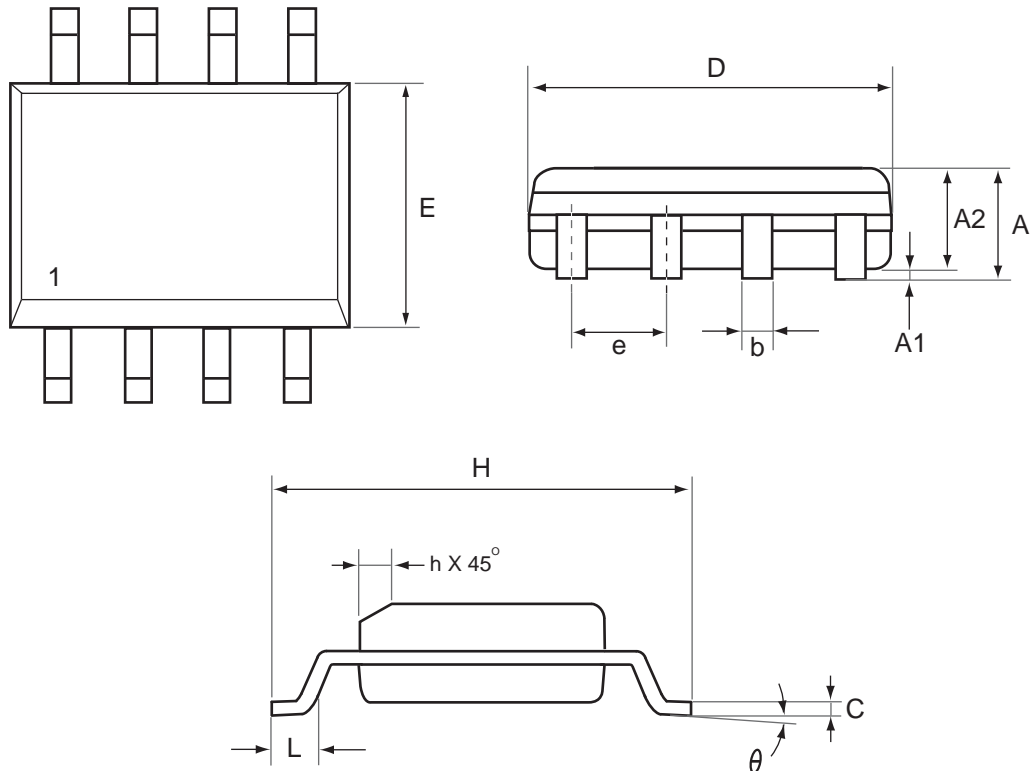
Unclamped Inductive Waveforms

Figure 13b.



## PACKAGE OUTLINE DIMENSIONS

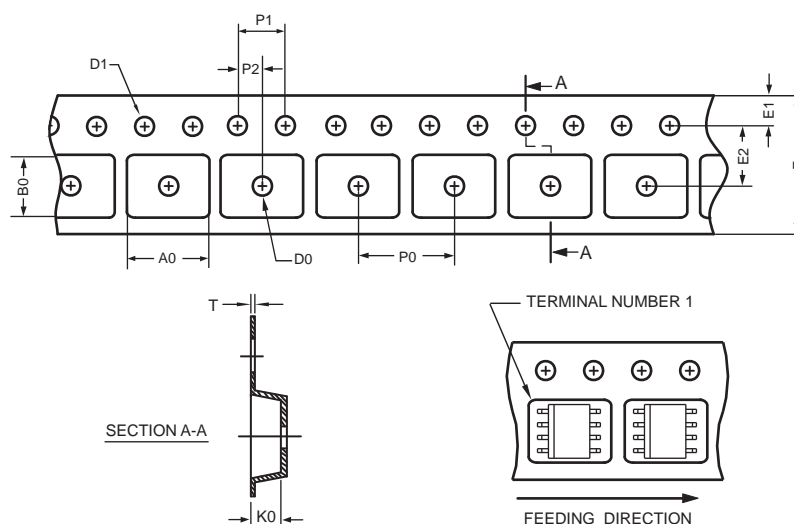
### SO-8



SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.35	1.75	0.053	0.069
A1	0.10	0.25	0.004	0.010
A2	1.25	1.63	0.049	0.064
b	0.31	0.51	0.012	0.020
C	0.17	0.25	0.007	0.010
D	4.80	5.00	0.189	0.197
E	3.70	4.00	0.146	0.157
e	1.27 REF.		0.050 BSC	
H	5.80	6.20	0.228	0.244
L	0.40	1.27	0.016	0.050
θ	0°	8°	0°	8°
h	0.25	0.50	0.010	0.020

## SO-8 Tape and Reel Data

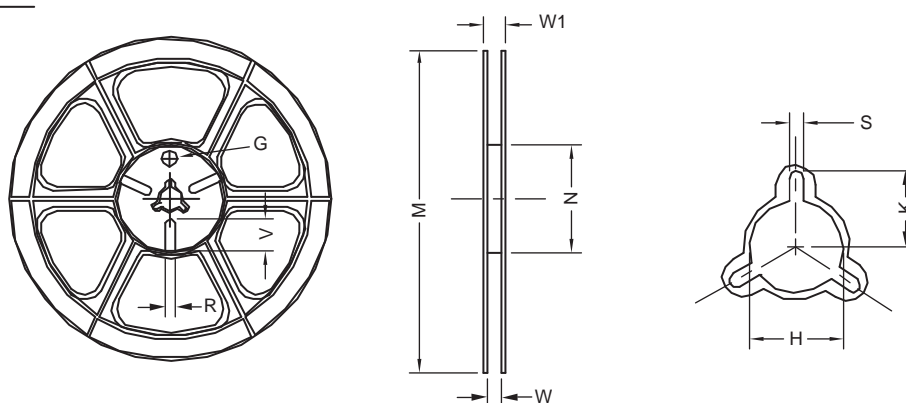
### SO-8 Carrier Tape



unit:mm

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
SOP 8N 150mil	6.50 ±0.15	5.25 ±0.10	2.10 ±0.10	φ 1.5 (MIN)	φ 1.55 ±0.10	12.0 +0.3 - 0.1	1.75 ±0.10	5.5 ±0.10	8.0 ±0.10	4.0 ±0.10	2.0 ±0.10	0.30 ±0.013

### SO-8 Reel



UNIT:mm

TAPE SIZE	REEL SIZE	M	N	W	W1	H	K	S	G	R	V
12 mm	φ 330	330 ± 1	62 ±1.5	12.4 + 0.2	16.8 - 0.4	φ 12.75 + 0.15	---	2.0 ±0.15	---	---	---

## TOP MARKING DEFINITION

